

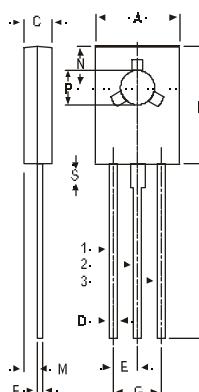
**TO-126 (SOT-32) Plastic Package**

**CSC1162**

**CSC1162 NPN PLASTIC POWER TRANSISTOR**

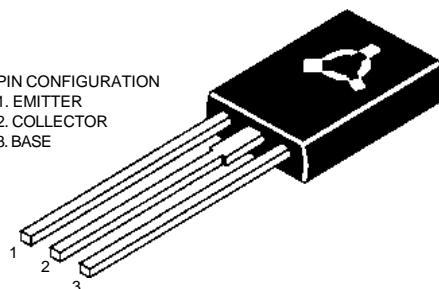
Complementary CSA715

Low frequency Power Amplifier



DIM	MIN.	MAX.
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 TYP.	
F	0.49	0.75
G	4.5 TYP.	
L	15.7 TYP.	
M	1.27 TYP.	
N	3.75 TYP.	
P	3.0	3.2
S	2.5 TYP.	

ALL DIMENSIONS IN MM



PIN CONFIGURATION  
1. Emitter  
2. Collector  
3. Base

**ABSOLUTE MAXIMUM RATINGS**

Collector-base voltage (open emitter)	V <sub>CBO</sub>	max.	35 V
Collector-emitter voltage (open base)	V <sub>CEO</sub>	max.	35 V
Collector current	I <sub>C</sub>	max.	2.5 A
Total power dissipation up to T <sub>C</sub> = 25 °C	P <sub>tot</sub>	max.	10 W
Junction temperature	T <sub>j</sub>	max.	150 °C
Collector-emitter saturation voltage I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A	V <sub>CEsat</sub>	max.	1.0 V
D.C. current gain I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 2V	h <sub>FE</sub>	min.	60
		max.	320

**RATINGS** (at T<sub>A</sub>=25 °C unless otherwise specified)

Limiting values			
Collector-base voltage (open emitter)	V <sub>CBO</sub>	max.	35 V
Collector-emitter voltage (open base)	V <sub>CEO</sub>	max.	35 V

Emitter-base voltage (open collector)	$V_{EBO}$	max.	5.0 V
Collector current	$I_C$	max.	2.5 A
Collector current (Peak)	$I_C$	max.	3.0 A
Total power dissipation up to $T_A = 25^\circ C$	$P_{tot}$	max.	0.75 W
Total power dissipation up to $T_C = 25^\circ C$	$P_{tot}$	max.	10 W
Junction temperature	$T_j$	max.	150 °C
Storage temperature	$T_{stg}$		65 to +150 °C

### CHARACTERISTICS

$T_{amb} = 25^\circ C$  unless otherwise specified

Collector cutoff current $I_E = 0; V_{CB} = 35V$	$I_{CBO}$	max.	20 $\mu A$
Breakdown voltages $I_C = 10 mA; I_B = 0$	$V_{CEO}$	min.	35 V
$I_C = 1 mA; I_E = 0$	$V_{CBO}$	min.	35 V
$I_E = 1 mA; I_C = 0$	$V_{EBO}$	min.	5 V
Saturation voltage $I_C = 2 A; I_B = 0.2 A$	$V_{CEsat}^*$	max.	1.0 V
Base-emitter on voltage $I_C = 1.5A; V_{CE} = 2V$ (Pulse)	$V_{BE(on)}$	max.	1.5 V
D.C. current gain $I_C = 0.5 A; V_{CE} = 2 V^{**}$	$h_{FE}$	min.	60
		max.	320
$I_C = 1.5 A; V_{CE} = 2 V$ (Pulse)	$h_{FE}$	min.	20
Transition frequency $I_C = 0.2 A; V_{CE} = 2 V$	$f_T$	typ.	180 MHz

\*\*  $h_{FE}$  classification: B: 60-120 C: 100-200 D: 160-320

## Disclaimer

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